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## Silicon Schottky Barrier Diode for High Speed Switching



ADE-208-965 (Z)

Rev.0 Aug. 2000

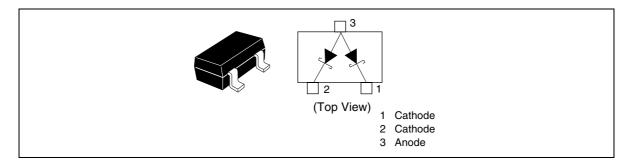
#### Features

- Low reverse current, Low capacitance.
- CMPAK package is suitable for high density surface mounting and high speed assembly.

#### **Ordering Information**

Туре No.	Laser Mark	Package Code
HSB88WA	C7	СМРАК

#### **Pin Arrangement**



#### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Value	Unit
Reverse voltage	V <sub>R</sub>	10	V
Average rectified current	l <sub>o</sub> *	15	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	–55 to +125	°C

Note: Per one device.

#### **Electrical Characteristics**

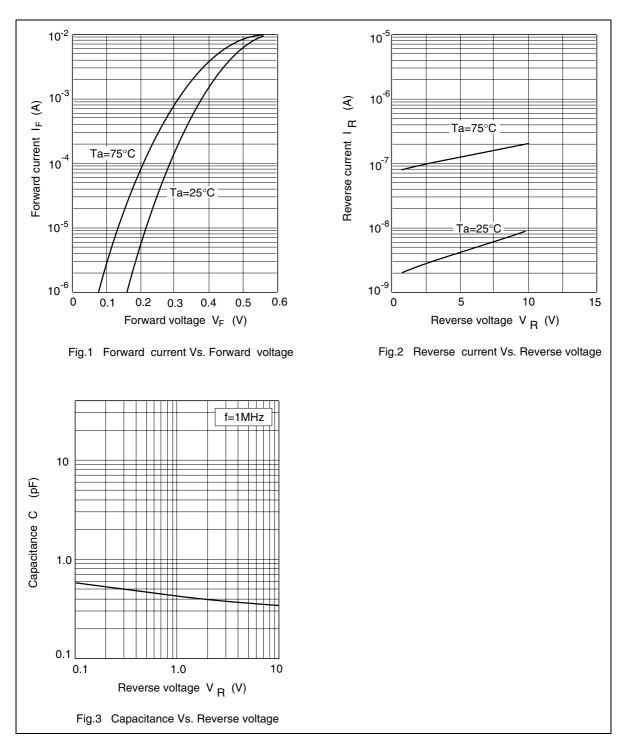
 $(Ta = 25^{\circ}C) *^{1}$ 

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Forward voltage	V <sub>F1</sub>	0.350	) —	0.420	V	I <sub>F</sub> = 1 mA
	V <sub>F2</sub>	0.500	) —	0.580	)	I <sub>F</sub> = 10 mA
Reverse current	I <sub>R1</sub>			0.2	μA	V <sub>R</sub> = 2 V
	I <sub>R2</sub>			10		V <sub>R</sub> = 10 V
Capacitance	С			0.80	pF	$V_{_{R}} = 0 V, f = 1 MHz$
Capacitance deviation	$\Delta C$		—	0.10	pF	$V_{_{\rm R}} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$
Forward voltage deviation	$\Delta V_{\rm F}$			10	mV	$I_{\rm F} = 10  {\rm mA}$
ESD-Capability *2		30	—	—	V	C = 200 pF, R = 0 $\Omega$ , Both forward and reverse direction 1 pulse.

Notes: 1. Per one device.

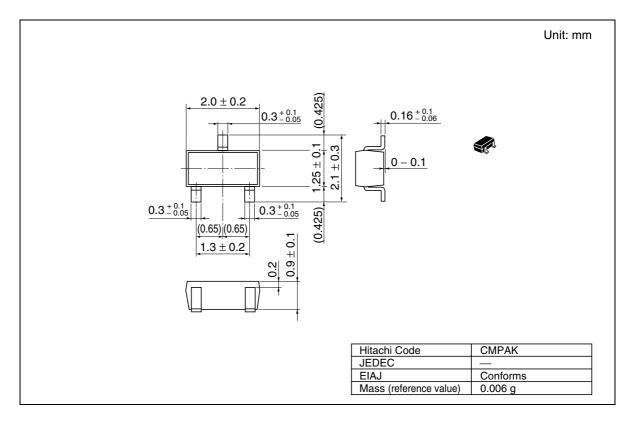
2. Failure criterion ;  $I_{_{\rm R}}\!>0.4~\mu A$  at  $V_{_{\rm R}}\!=$  2 V

#### **Main Characteristic**



RENESAS

#### **Package Dimensions**





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